

Dual P-Channel 20-V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	$R_{DS(on)}\left(\Omega\right)$	I _D (A)			
- 20	$0.019 \text{ at V}_{GS} = -10 \text{ V}$	- 8.4			
	0.031 at V _{GS} = - 4.5 V	- 6.7			

FEATURES

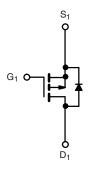
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET
- 100 % R_g Tested
- Compliant to RoHS Directive 2002/95/EC

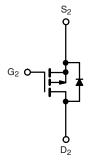
Pb-free RoHS



APPLICATIONS

- · Load Switching
 - Computer
 - Game Systems
- · Battery Switching
 - 2-Cell Li-Ion





P-Channel MOSFET

P-Channel MOSFET

		SO-8		
S ₁	1		8	D ₁
G_1	2		7	D_1
S_2	3		6	D_2
G_2	4		5	D_2
		Top View		

Ordering Information: Si4943BDY-T1-E3 (Lead (Pb)-free) Si4943BDY-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted						
Parameter		Symbol	10 s	Steady State	Unit	
Drain-Source Voltage		V _{DS}	- 20		V	
Gate-Source Voltage		V _{GS}	± 20			
Ocation - Decis Ocate /T 450 00)8	T _A = 25 °C	- I _D	- 8.4	- 6.3		
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C		- 6.7	- 5.1	Δ.	
Pulsed Drain Current		I _{DM}	- 30		Α	
Continuous Source Current (Diode Conduction) ^a		I _S	- 1.7	- 0.9		
	T _A = 25 °C	В	2.0	1.1	W	
Maximum Power Dissipation ^a	T _A = 70 °C	- P _D	1.3	0.7	VV	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Manifestory Investigation to Application 19	t ≤ 10 s	R _{thJA}	46	62.5		
Maximum Junction-to-Ambient ^a	Steady State	' 'thJA	85	110	°C/W	
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	26	35		

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

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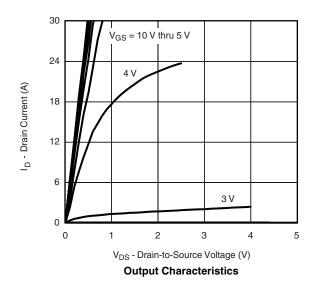
SPECIFICATIONS $T_J = 25$ °C, unless otherwise noted							
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = -250 \mu A$	- 1		- 3	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zava Cata Valtana Duais Courset		V _{DS} = - 20 V, V _{GS} = 0 V			- 1	- 1 - 5 μA	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = -20 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$			- 5		
On-State Drain Current ^a	I _{D(on)}	V _{DS} = - 5 V, V _{GS} = - 10 V	- 30			Α	
D : 0	D	V _{GS} = - 10 V, I _D = - 8.4 A		0.016	0.019	0	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 4.5 V, I _D = - 6.7 A		0.026	0.031	Ω	
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 10 V, I _D = - 8.4 A		20		S	
Diode Forward Voltage ^a	V _{SD}	I _S = - 1.7 A, V _{GS} = 0 V		- 0.75	- 1.2	V	
Dynamic ^b							
Total Gate Charge	Q_g			17	25		
Gate-Source Charge	Q_{gs}	$V_{DS} = -10 \text{ V}, V_{GS} = -5 \text{ V}, I_{D} = -8.4 \text{ A}$		5		nC	
Gate-Drain Charge	Q_{gd}			6.7			
Gate Resistance	R_g	f = 1 MHz	2.4	12	18	Ω	
Turn-On Delay Time	t _{d(on)}			11	17		
Rise Time	t _r	V_{DD} = - 10 V, R_L = 10 Ω		10	15		
Turn-Off Delay Time	t _{d(off)}	$I_D\cong$ - 1 A, $V_{GEN}=$ - 10 V, $R_g=$ 6 Ω		94	140	ns	
Fall Time	t _f			60	90		
Source-Drain Reverse Recovery Time	t _{rr}	I _F = - 1.7 A, dl/dt = 100 A/μs		55	80		

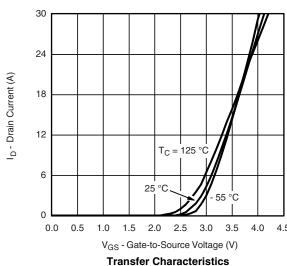
Notes:

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

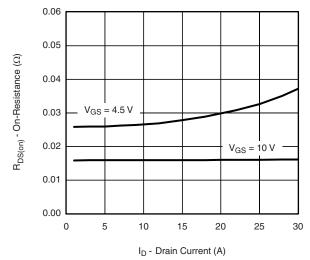
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



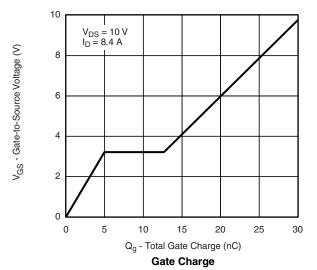


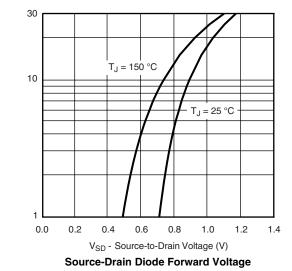


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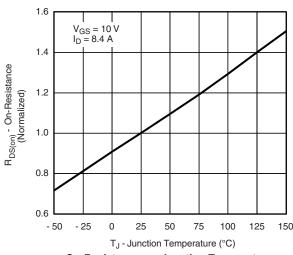


On-Resistance vs. Drain Current

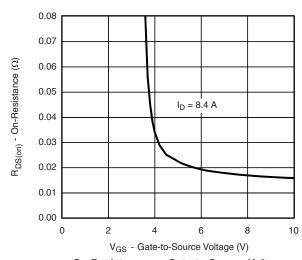




2100 1800 Ciss 1500 C - Capacitance (pF) 1200 900 600 $\mathsf{C}_{\mathsf{oss}}$ 300 0 0 8 12 16 20



On-Resistance vs. Junction Temperature



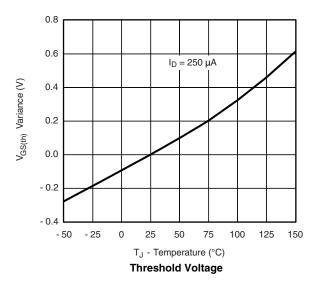
On-Resistance vs. Gate-to-Source Voltage

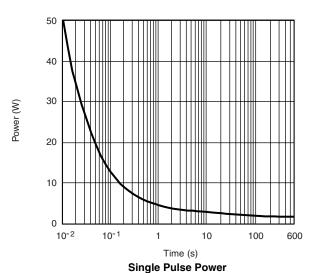
S - Source Current (A)

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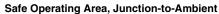
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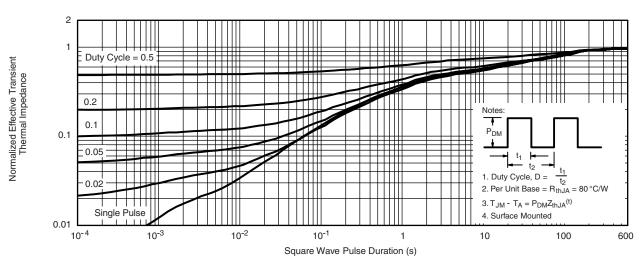
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





 $\begin{array}{c} \text{Limited by } R_{DS(on)}^{*} \\ \text{10} \\$

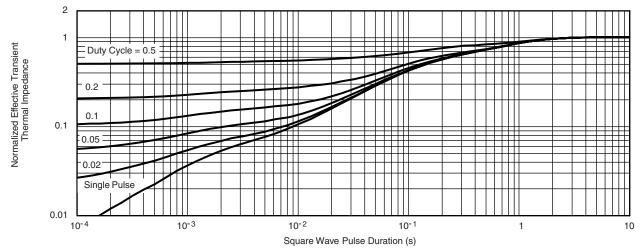




Normalized Thermal Transient Impedance, Junction-to-Ambient



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Foot

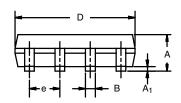
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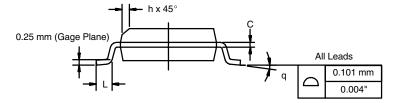
Document Number: 73073 S09-0704-Rev. C, 27-Apr-09



SOIC (NARROW): 8-LEAD JEDEC Part Number: MS-012







	MILLIM	IETERS	INCHES			
DIM	Min	Max	Min	Max		
Α	1.35	1.75	0.053	0.069		
A ₁	0.10	0.20	0.004	0.008		
В	0.35	0.51	0.014	0.020		
С	0.19	0.25	0.0075	0.010		
D	4.80	5.00	0.189	0.196		
Е	3.80	4.00	0.150	0.157		
е	1.27	BSC	0.050 BSC			
Н	5.80	6.20	0.228	0.244		
h	0.25	0.50	0.010	0.020		
L	0.50	0.93	0.020	0.037		
q	0°	8°	0°	8°		
S	0.44	0.64	0.018	0.026		
ECN: C-06527-Rev. I. 11-Sep-06						

DWG: 5498

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RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads Dimensions in Inches/(mm)

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